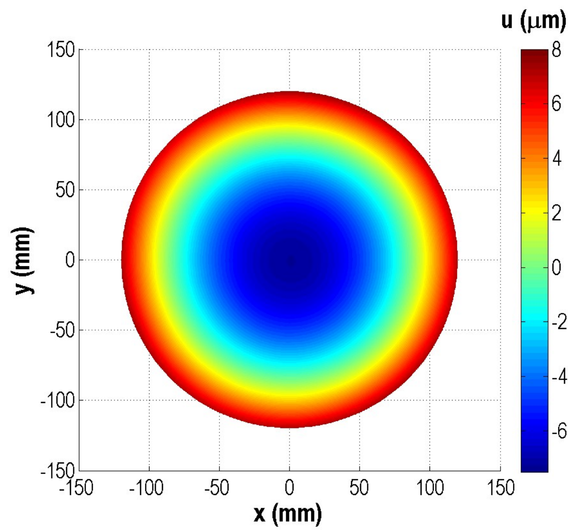

Figure-1: Induced displacement on 300mm Si wafer by deposition of 108nm Al2O3 deposited at 190°C.

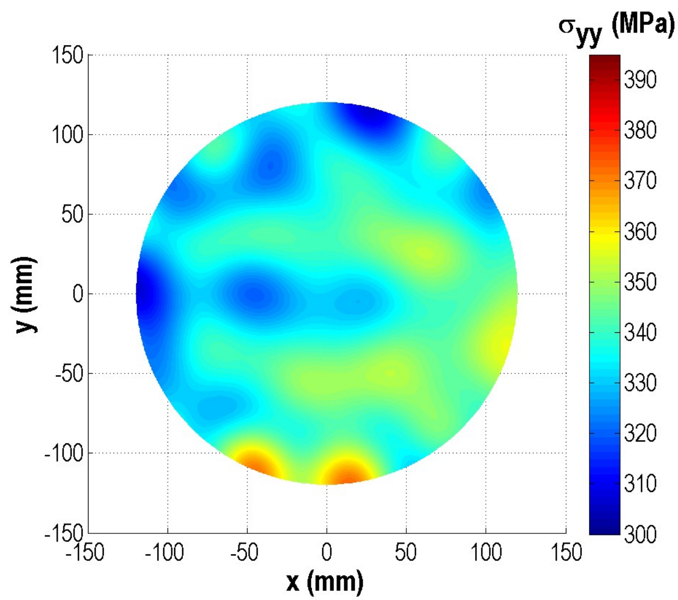

Figure-2: In plane intrinsic film stress of 108nm Al2O3 deposited at 190°C. Average stress is 338MPa. Non-uniformity (1σ) = 9.6MPa